



IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

In re Application of:

DISNEY, D.

Serial No.: 10/647,925

Filing Date: August 26, 2003

For: High-Voltage Transistor With Buried

Conduction Layer

Examiner:

Loke, Steven Ho Yin

Art Unit:

2811

Information Disclosure Statement

Commissioner for Patents P.O. Box 1450 Alexandria, VA 22313-1450

Sir:

Enclosed is a copy of Information Disclosure Citation Form PTO-1449A together with a copy of the documents cited on that form. It is respectfully requested that the cited documents be considered and that the enclosed copy of Information Disclosure Citation Form PTO-1449A be initialed by the Examiner to indicate such consideration and a copy thereof returned to applicant(s).

Pursuant to 37 C.F.R. § 1.97, the submission of this Information Disclosure Statement is not to be construed as a representation that a search has been made and is not to be construed as an admission that the information cited in this statement is material to patentability.

Pursuant to 37 C.F.R. § 1.97, this Information Disclosure Statement is being submitted under one of the following (as indicated by an "X" to the left of

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XX A check	A check for \$180.00 for the fee under 37 C.F.R. § 1.17(p).							
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(2) A su	(2) A check for \$180.00 for the fee under 37 C.F.R. §1.17(p) for submission of the Information Disclosure Statement.							
Please charge an	y shortages of fees or credit any overcharges of fees to our							
Deposit Account No. 50-	2060.							
Dated: 4/30_, 20	Respectfully submitted, BURGESS & BEREZNAK, LLP Bradley J. Bereznak Attorney for Applicant Registration No. 33,474							
	FIRST CLASS CERTIFICATE OF MAILING (37 C.F.R. § 1.8(a))							
United States Postal Service	oing INFORMATION DISCLOSURE STATEMENT is being deposited with the as first class mail with sufficient postage in an envelope addressed to the O. Box 1450, Alexandria, VA 22313-1450 onApril 30, 2004							
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